

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

MJE2360T
MJE2361T

NPN HIGH VOLTAGE
POWER TRANSISTOR

JEDEC TO-220 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR MJE2360T and MJE2361T types are NPN Silicon Power Transistors designed for high voltage applications such as power supplies and other switching applications.

MAXIMUM RATINGS ($T_C=25^\circ\text{C}$)

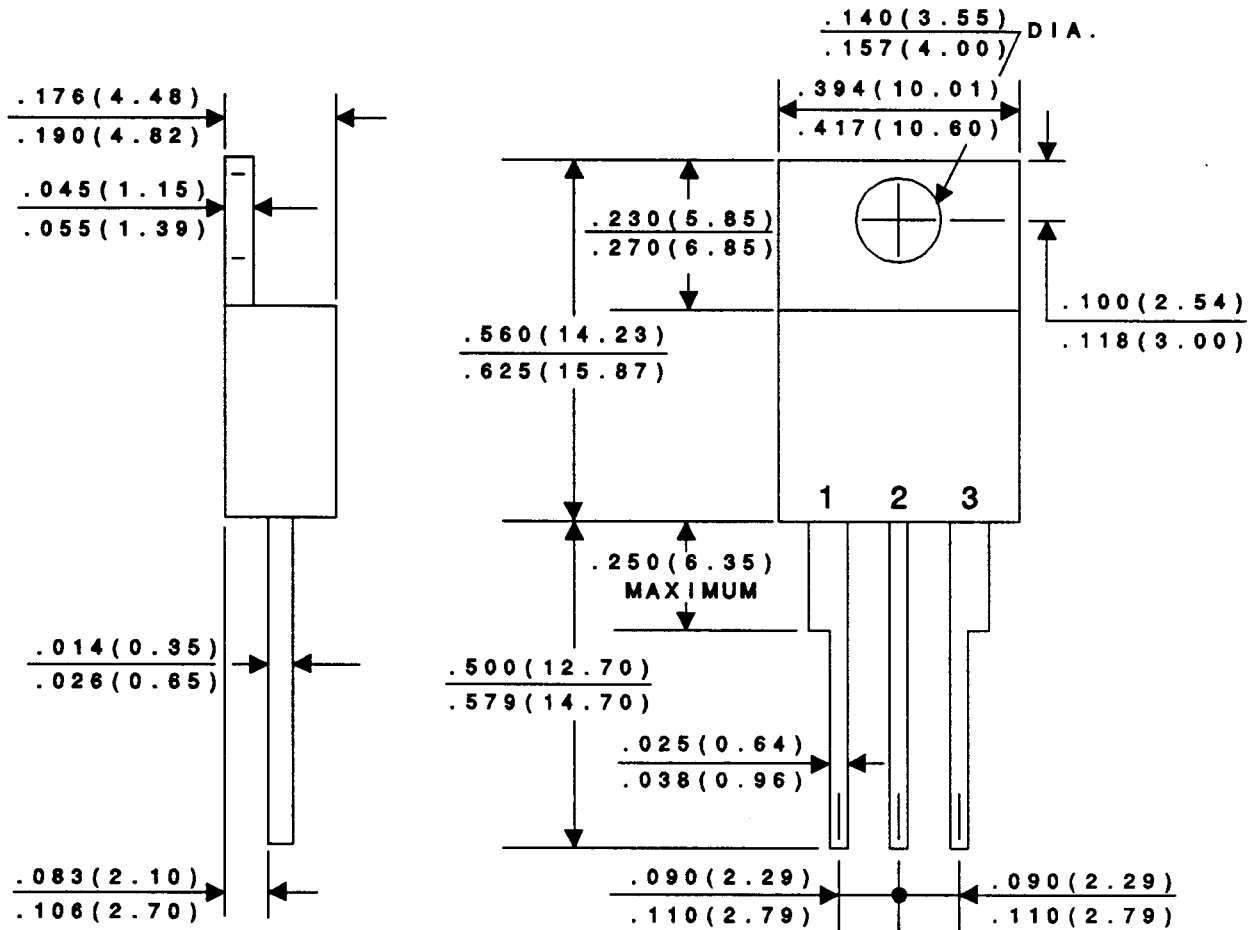
	<u>SYMBOL</u>		<u>UNITS</u>
Collector-Base Voltage	V_{CBO}	375	V
Collector-Emitter Voltage	V_{CEO}	350	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	500	mA
Base Current	I_B	250	mA
Power Dissipation	P_D	30	W
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JC}	4.167	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>TYP</u>	<u>MAX</u>	<u>UNITS</u>
I_{CEV}	$V_{CE}=375\text{V}, V_{EB(\text{off})}=1.5\text{V}$			500	μA
I_{CEO}	$V_{CE}=250\text{V}$			250	μA
I_{CBO}	$V_{CB}=375\text{V}$			100	μA
I_{EBO}	$V_{EB}=5.0\text{V}$			100	μA
BV_{CEO}	$I_C=2.5\text{mA}$	350			V
$V_{CE(\text{SAT})}$	$I_C=100\text{mA}, I_B=10\text{mA}$			1.5	V
$V_{BE(\text{ON})}$	$V_{CE}=10\text{V}, I_C=100\text{mA}$			1.0	V
h_{FE}	$V_{CE}=10\text{V}, I_C=50\text{mA}$ (MJE2360T)	25		200	
h_{FE}	$V_{CE}=10\text{V}, I_C=50\text{mA}$ (MJE2361T)	50		250	
h_{FE}	$V_{CE}=10\text{V}, I_C=100\text{mA}$ (MJE2360T)	15			
h_{FE}	$V_{CE}=10\text{V}, I_C=100\text{mA}$ (MJE2361T)	40			
f_T	$V_{CE}=10\text{V}, I_C=50\text{mA}, f=1.0\text{MHz}$		10		MHz
C_{ob}	$V_{CB}=100\text{V}, I_E=0, f=100\text{kHz}$		20		pF

(SEE REVERSE SIDE)

JEDEC TO-220 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm).

LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER

NOTE: TAB IS COMMON TO PIN 2